

36316-SC



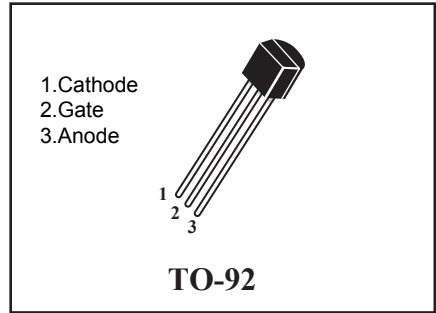
MCR100-6/MCR100-8

**Sensitive Gate Silicon Controlled Rectifiers
Reverse Blocking Thyristors**

Lead(Pb)-Free



SCRs
0.8 A RMS
400/600 Voltage



Maximum Ratings ($T_A=25^{\circ}\text{C}$ unless otherwise noted)

Rating	Symbol	MCR100-6	MCR100-8	Unit
Repetitive Peak Off-stage Voltage	V_{DRM}	400	600	V
Collector-Base Voltage	I_{TRMS}	0.8		A
Junction Temperature Range	T_J	+150		$^{\circ}\text{C}$
Storage Temperature Range	T_{stg}	-55 to +150		$^{\circ}\text{C}$

ELECTRICAL CHARACTERISTICS

Characteristics	Symbol	Min	Max	Unit	
On State Voltage ⁽¹⁾ $I_{TM} = 1\text{A}$	V_{TM}	-	1.7	V	
Gate Trigger Voltage $V_{AK} = 7\text{V}$	V_{GT}	-	0.8	V	
Peak Repetitive Forward and Reverse Blocking Voltage $I_{DRM} = 10\mu\text{A}$, $V_{MAX} = 10\text{V}$	MCR100-6 MCR100-8 V_{DRM}, V_{RRM}	400 600	-	V	
Peak Forward or Reverse Blocking Current $V_{AK} = \text{Rated}$, V_{DRM} or V_{RRM}	I_{DRM}, I_{RRM}	-	10	μA	
Holding Current $I_{HL} = 20\text{mA}$, $A_V = 7\text{V}$	I_H	-	5	mA	
Gate Trigger Current $V_{AK} = 7\text{V}$	I_{GT}	A2 A1 A B	5 15 30 80	15 30 80 200	μA

Note 1. Forward current applied for 1 ms maximum duration, duty cycle $\leq 1\%$